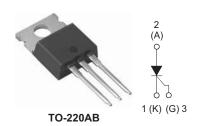




Vishay High Power Products

Phase Control SCR, 12.5 A



PRODUCT SUMMARY			
V _T at 8 A 1.2 V			
I _{TSM}	140 A		
V _{RRM}	800 V		

DESCRIPTION/FEATURES

The 12TTS08 High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification and crowbar (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

Also available in SMD-220 package (series 12TTS..S)

This product has been designed and qualified for industrial level.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W	13.5	17	А		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	8	٨		
I _{T(RMS)}		12.5	Α		
V _{DRM} /V _{RRM}		800	V		
I _{TSM}		140	Α		
V _T	8 A, T _J = 25 °C	1.2	V		
dV/dt		150	V/µs		
dl/dt		100	A/µs		
TJ	Range	- 40 to 125	°C		

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} , MAXIMUM PEAK VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
12TTS08	800	800	1.0		

Document Number: 93694 Revision: 02-Jun-08

12TTS08 High Voltage Series

Vishay High Power Products Phase Control SCR, 12.5 A



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T 400 00 4000 and attimated to the first and a		8	
Maximum RMS on-state current	I _{T(RMS)}	1 _C = 108 °C,	T _C = 108 °C, 180° conduction, half sine wave		
Maximum peak, one-cycle,	I	10 ms sine pu	ulse, rated V _{RRM} applied, T _J = 125 °C	120	A
non-repetitive surge current	I _{TSM}	10 ms sine pu	ulse, no voltage reapplied, T _J = 125 °C	140	
Maximum 12+ for fusing	l²t	10 ms sine pu	ulse, rated V _{RRM} applied, T _J = 125 °C	72	A ² s
Maximum I ² t for fusing	I-t	10 ms sine pu	ulse, no voltage reapplied, T _J = 125 °C	100	A-S
Maximum I $^2\sqrt{t}$ for fusing	I ² √t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = 125$ °C		1000	A²√s
Maximum on-state voltage drop	V_{TM}	8 A, T _J = 25 °C		1.2	V
On-state slope resistance	r _t	$ T_{\text{T}} = 125 ^{\circ}\text{C} $		16.2	mΩ
Threshold voltage	V _{T(TO)}			0.87	V
Maximum various and divest leakage current	1 //	T _J = 25 °C	V Poted V A	0.05	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T _J = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1.0	
Typical holding current	l _Η	Anode supply = 6 V, resistive load, initial $I_T = 1 A$		30	mA
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		50	
Maximum rate of rise of off-state voltage	dV/dt	T _J = 25 °C		150	V/µs
Maximum rate of rise of turned-on current	dl/dt			100	A/µs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	$P_{G(AV)}$		2.0	VV	
Maximum peak positive gate current	+ I _{GM}		1.5	Α	
Maximum peak negative gate voltage	- V _{GM}		10	V	
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	20	mA	
		Anode supply = 6 V, resistive load, T _J = 25 °C	15		
		Anode supply = 6 V, resistive load, T _J = 125 °C	10		
	Anode supply = 6 V, resistive load, T_J = - 65 °C Anode supply = 6 V, resistive load, T_J = 25 °C Anode supply = 6 V, resistive load, T_J = 125 °C	Anode supply = 6 V, resistive load, T _J = - 65 °C	1.2		
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	1	v	
		Anode supply = 6 V, resistive load, T _J = 125 °C	0.7	V	
Maximum DC gate voltage not to trigger	V_{GD}	$T_{J} = 125 ^{\circ}\text{C}, V_{DRM} = \text{Rated value} $			
Maximum DC gate current not to trigger	I_{GD}			mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8	
Typical reverse recovery time	t _{rr}	T 105 °C	3	μs
Typical turn-off time	tq	T _J = 125 °C	100	



12TTS08 High Voltage Series

Phase Control SCR, 12.5 A Vishay High Power Products

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T_J , T_{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R_{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
	minimum			6 (5)	kgf ⋅ cm
Mounting torque	maximum			12 (10)	(lbf \cdot in)
Marking device			Case style TO-220AB	12TTS08	

Document Number: 93694 Revision: 02-Jun-08

Vishay High Power Products Phase Control SCR, 12.5 A



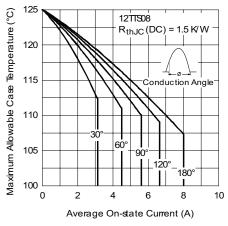


Fig. 1 - Current Ratings Characteristics

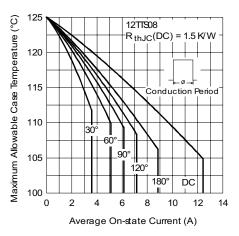


Fig. 2 - Current Ratings Characteristics

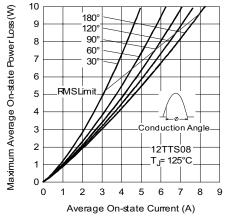


Fig. 3 - On-State Power Loss Characteristics

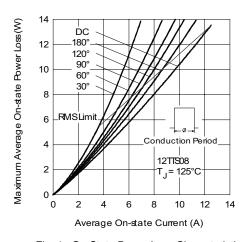


Fig. 4 - On-State Power Loss Characteristics

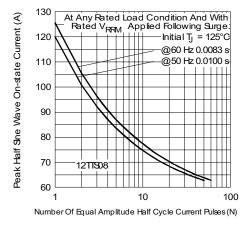


Fig. 5 - Maximum Non-Repetitive Surge Current

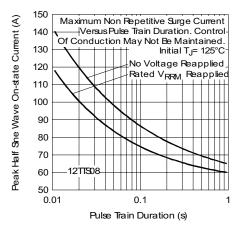


Fig. 6 - Maximum Non-Repetitive Surge Current



Phase Control SCR, 12.5 A Vishay High Power Products

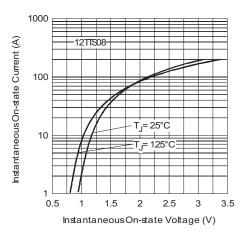


Fig. 7 - On-State Voltage Drop Characteristics

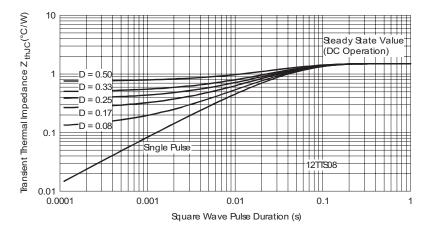


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

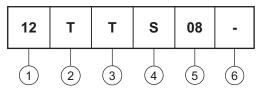
12TTS08 High Voltage Series

Vishay High Power Products Phase Control SCR, 12.5 A



ORDERING INFORMATION TABLE

Device code



- Current ratings (12 = 12.5 A)

2 - Circuit configuration:

T = Single thyristor

3 - Package:

T = TO-220

4 - Type of silicon:

S = Standard recovery rectifier

5 - Voltage rating (08 = 800 V)

None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS			
Dimensions http://www.vishay.com/doc?95222			
Part marking information	http://www.vishay.com/doc?95225		

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